Transient Voltage Suppressors

Low Capacitance ESD Protection for High Speed Data

The NUP2114 transient voltage suppressor is designed to protect high speed data lines from ESD. Ultra-low capacitance and high level of ESD protection makes this device well suited for use in USB 2.0 applications.

Features

- Low Capacitance 0.8 pF
- Low Clamping Voltage
- Stand Off Voltage: 5 V
- Low Leakage
- ESD Rating of Class 3B (Exceeding 8 kV) per Human Body model and Class C (Exceeding 400 V) per Machine Model
- Protection for the Following IEC Standards: IEC 61000–4–2 Level 4 ESD Protection
- UL Flammability Rating of 94 V-0
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- High Speed Communication Line Protection
- USB 2.0 High Speed Data Line and Power Line Protection
- Monitors and Flat Panel Displays
- MP3
- Gigabit Ethernet
- Notebook Computers
- Digital Video Interface (DVI) and HDMI

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	TL	260	°C
Human Body Model (HBM) Machine Model (MM) IEC 61000-4-2 Contact IEC61000-4-2 Air	ESD	16000 400 13000 15000	٧

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

See Application Note AND8308/D for further description of survivability specs.



ON Semiconductor®

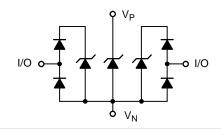
www.onsemi.com



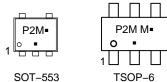


CASE 463B

TSOP-6 CASE 318G



MARKING DIAGRAMS



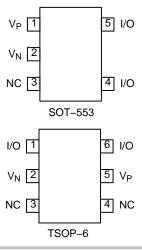
P2, P2M = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



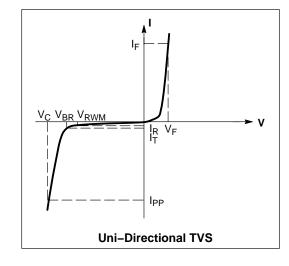
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

	<u>'</u>
Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V_{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V_{BR}	Breakdown Voltage @ I _T
Ι _Τ	Test Current
I _F	Forward Current
V _F	Forward Voltage @ I _F
P _{pk}	Peak Power Dissipation
С	Max. Capacitance @ V _R = 0 and f = 1.0 MHz



^{*}See Application Note AND8308/D for detailed explanations of datasheet parameters.

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}	(Note 1)			5.0	V
Breakdown Voltage	V_{BR}	I _T = 1 mA, (Note 2)	5.5	7.5		V
Reverse Leakage Current	I _R	V _{RWM} = 5 V		0.01	1.0	μΑ
Clamping Voltage	V _C	I _{PP} = 5 A (Note 3)		9.0		V
Clamping Voltage	V _C	I _{PP} = 8 A (Note 3)		10		V
Maximum Peak Pulse Current	I _{PP}	8x20 μs Waveform			12	Α
Junction Capacitance	CJ	V _R = 0 V, f = 1 MHz between I/O Pins and GND		0.8	1.0	pF
Junction Capacitance	CJ	V _R = 0 V, f = 1 MHz between I/O Pins			0.5	pF
Clamping Voltage	V _C	@ I _{PP} = 1 A (Note 4)			12	V
Clamping Voltage	V _C	Per IEC 61000-4-2 (Note 5)	Fi	gures 1 and	2	V

- TVS devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
- 2. V_{BR} is measured at pulse test current I_T.
- 3. Nonrepetitive current pulse (Pin 5 to Pin 2)
- 4. Surge current waveform per Figure 5.
- 5. Typical waveform. For test procedure see Figures 3 and 4 and Application Note AND8307/D.
- 6. Include S-prefix devices where applicable.

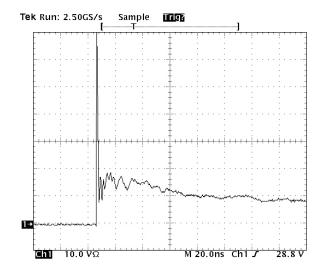


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

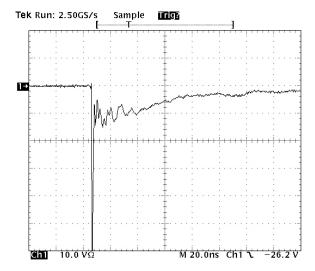


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

IEC 61000-4-2 Spec.

	-			
Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

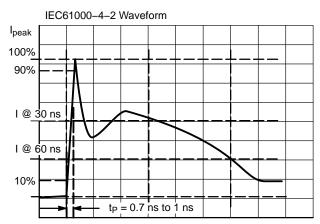


Figure 3. IEC61000-4-2 Spec

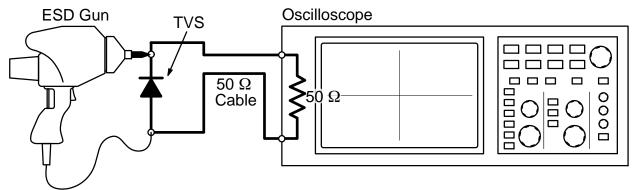


Figure 4. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

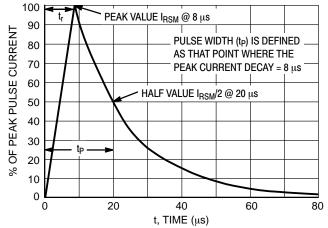


Figure 5. 8 X 20 μs Pulse Waveform

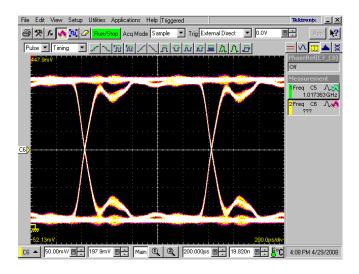


Figure 6. 500 MHz Data Pattern

ORDERING INFORMATION

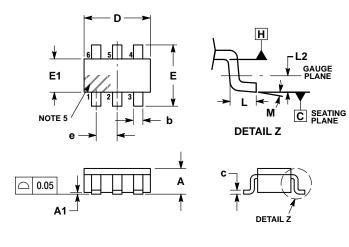
Device	Marking	Package	Shipping [†]
NUP2114UPXV5T1G	P2	SOT-553 (Pb-Free)	4,000 / Tape & Reel
NUP2114UCMR6T1G	P2M	TSOP-6 (Pb-Free)	3,000 / Tape & Reel
SNUP2114UCMR6T1G*	P2M	TSOP-6 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

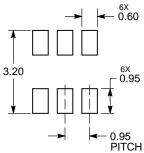
TSOP-6 CASE 318G-02 ISSUE V



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
 5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	0.90	1.00	1.10		
A1	0.01	0.06	0.10		
b	0.25	0.38	0.50		
С	0.10	0.18	0.26		
D	2.90	3.00	3.10		
Е	2.50	2.75	3.00		
E1	1.30	1.50	1.70		
е	0.85	0.95	1.05		
L	0.20	0.40	0.60		
L2	0.25 BSC				
М	Uo.		10°		

RECOMMENDED SOLDERING FOOTPRINT*

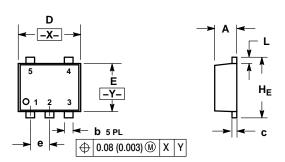


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-553, 6 LEAD CASE 463B ISSUE C



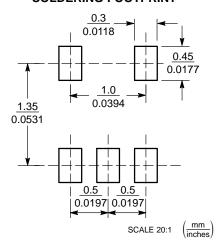
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS

 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.13	0.18	0.003	0.005	0.007
D	1.55	1.60	1.65	0.061	0.063	0.065
E	1.15	1.20	1.25	0.045	0.047	0.049
е	0.50 BSC 0.020 BSC					
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.55	1.60	1.65	0.061	0.063	0.065

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Phone: 81–3–5817–1050